

This diagram shows a cross-sectional view of a semiconductor device. A substrate 102 is at the bottom, with a layer 180a on its top surface. Two active regions are formed on the substrate, each containing a stack of layers: 110a and 118a in the left region, and 110b and 118b in the right region. These regions are separated by a central channel 120a. Above the active regions, there is a layer 122, and a top surface 100 is indicated. Various other labels like 108a, 114a, 116a, 120b, 108b, 114b, 116b, and 120a point to specific features and boundaries within the device structure.

FIG 1

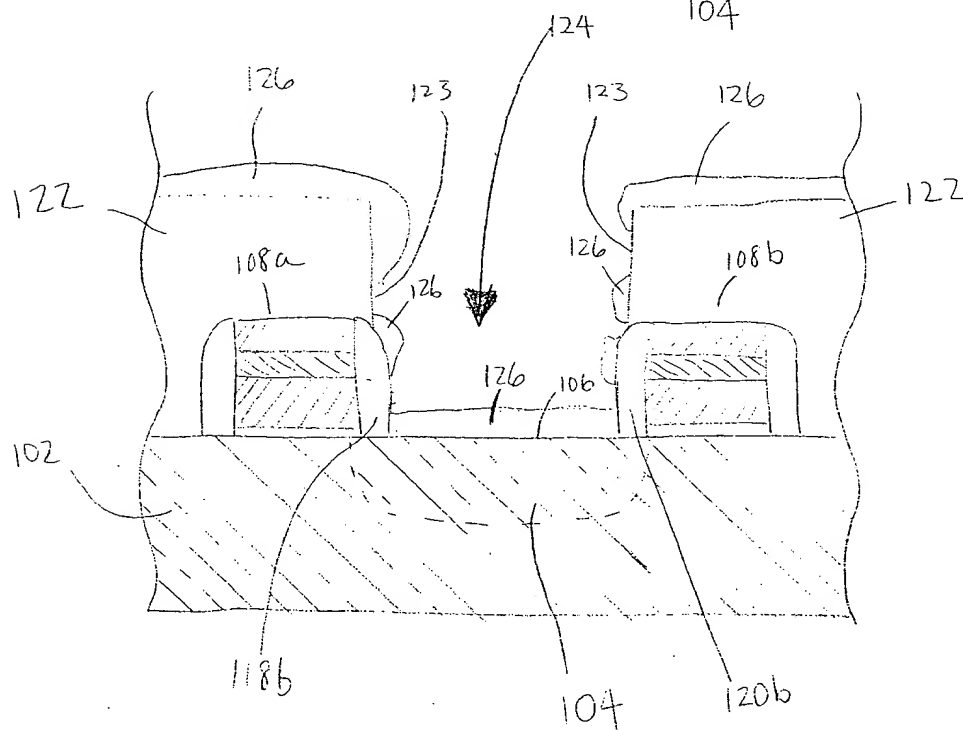


FIG. 2

FIG. 3

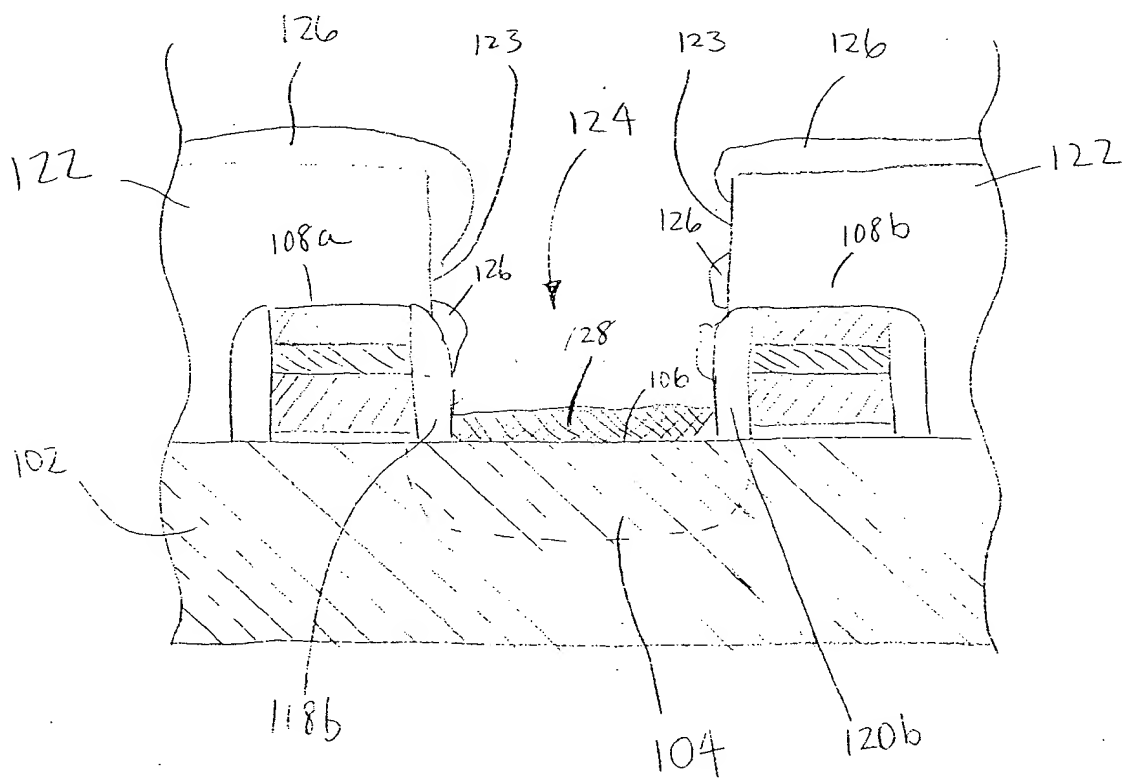


FIG. 3

FIG. 4

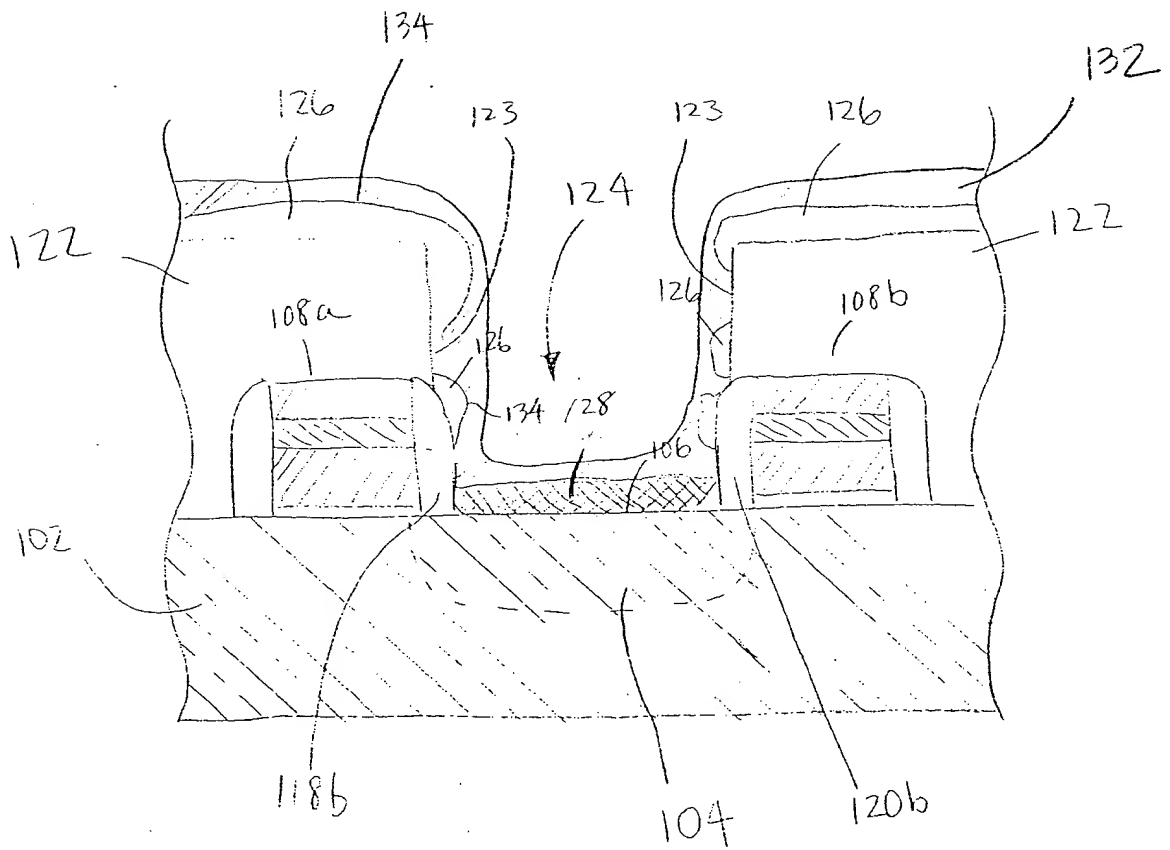


FIG 4

FIG. 5

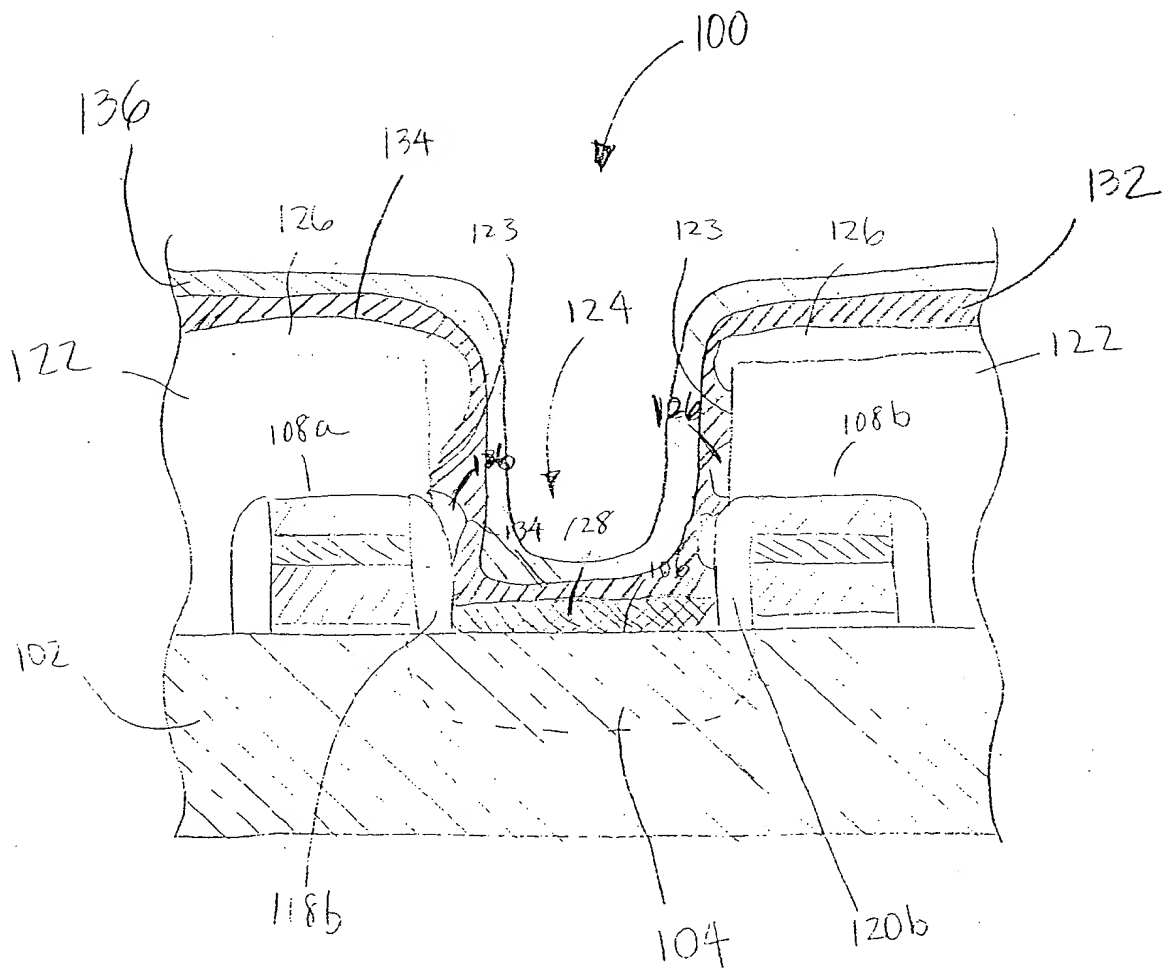


FIG 5

FIG. 6

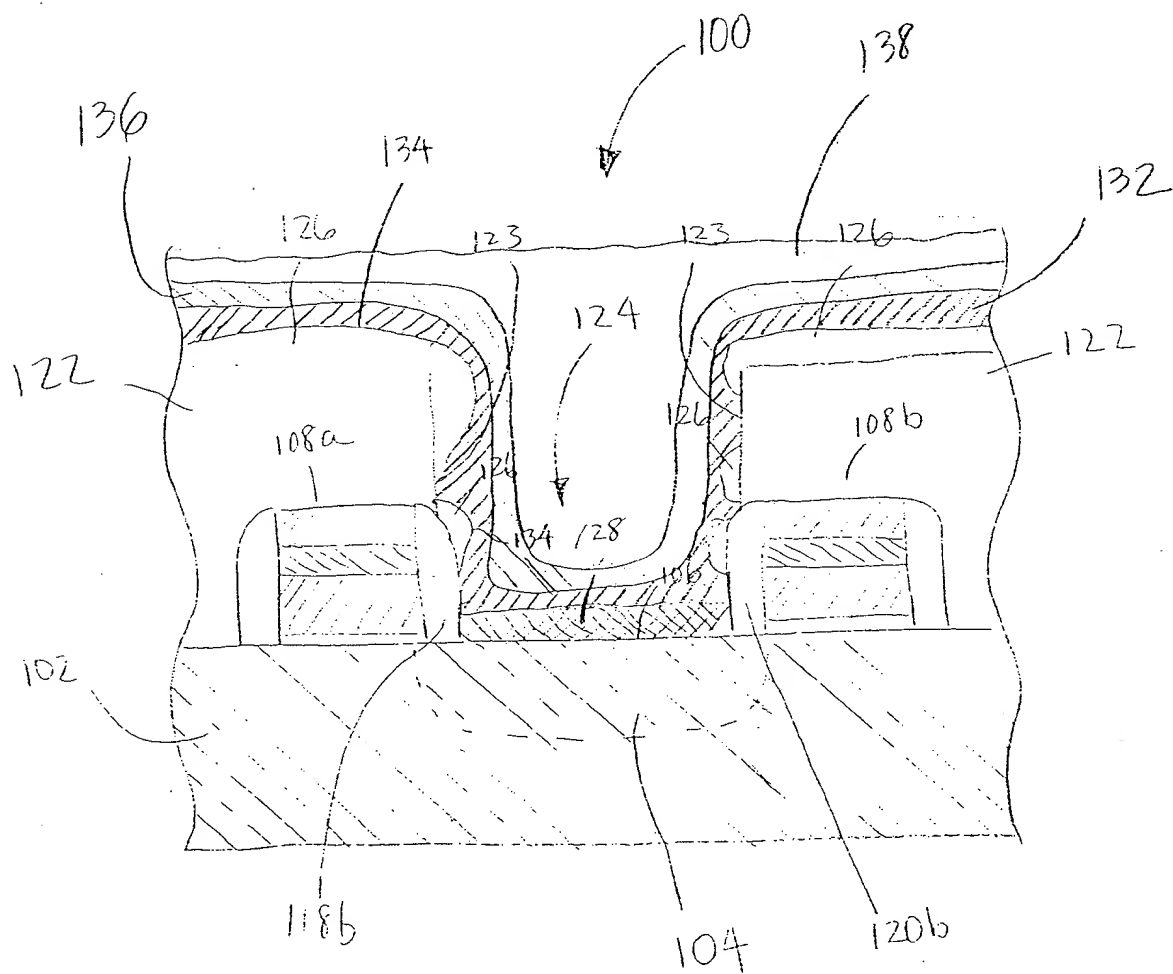


FIG 6